

IN THE CLAIMS

1. (Currently Amended) A semiconductor laser light emitting device comprising:
a stack of group III nitride semiconductor films;
wherein each group III nitride semiconductor film comprises an element selected from the group consisting of aluminum, gallium, indium, and boron;
wherein, an upper portion of said stack of group III nitride semiconductor films ~~comprises~~ is formed into a ridge-like stripe, to form a current injection region;
wherein a current injection width W_{st} of said current injection region is at a value in a range of $1\ \mu\text{m} \leq W_{st} \leq 3\ \mu\text{m}$; and
wherein said current injection region is formed on an active layer;
a current non-injection region formed on both sides of said ridge-like strip current injection region, wherein said current non-injection region comprises a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$, wherein the component ratio "x" of Al is at a value in a range of $0.3 \leq x \leq 1.0$; and
~~wherein the group III nitride semiconductor films~~ a film located between the active layer and the current non-injection region, ~~comprises~~ comprising a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0.3 \leq x \leq 1.0$), and ~~have~~ having a combined thickness of less than or equal to $0.2\ \mu\text{m}$ but greater than zero.

Claims 2-4 (Cancelled)

5. (Original) A semiconductor laser light emitting device according to claim 1, wherein a difference Δn between an effective refractive index n_1 of said current injection region in the film stacking direction and an effective refractive index n_2 of said current non-injection region in the film stacking direction is in a range of $0.007 \leq \Delta n = (n_1 - n_2) \leq 0.012$.

Claims 6-8 (Cancelled)

9. (Currently Amended) A semiconductor laser light emitting device comprising:
a stack of group III nitride semiconductor films;

wherein each group III nitride semiconductor film comprises an element selected from the group consisting of aluminum, gallium, indium, and boron;

wherein, an upper portion of said stack of group III nitride semiconductor films comprises is formed into a ridge-like stripe, to form a current injection region;

wherein a current injection width W_{st} of said current injection region is at a value in a range of $1 \mu m \leq W_{st} \leq 3 \mu m$; and

wherein said current injection region is formed on an active layer;

a current non-injection region formed on both sides of said ridge-like strip current injection region, wherein said current non-injection region comprises a material expressed by a chemical formula $Al_xGa_{1-x}N$, wherein the component ratio "x" of Al is at a value in a range of $0.15 < x < 0.30$; and

wherein the group III nitride semiconductor films located between the active layer and the current non-injection region, comprises a material expressed by a chemical formula $Al_xGa_{1-x}N$.

xN ($0.15 \leq x \leq 0.30$), and have a combined thickness of less than or equal to $0.2 \mu\text{m}$ but greater than zero.

Claims 10-12 (Cancelled)

13. (Original) A semiconductor laser light emitting device according to claim 9, wherein a difference Δn between an effective refractive index n_1 of said current injection region in the film stacking direction and an effective refractive index n_2 of said current non-injection region in the film stacking direction is in a range of $0 < \Delta n = (n_1 - n_2) < 0.007$.

Claims 14-24 (Cancelled)

25. (Currently Amended) A semiconductor laser light emitting device comprising:
a stack of group III nitride semiconductor films each comprising at least one element selected from the group of aluminum, gallium, indium, and boron;
an upper portion of said stack of group III nitride semiconductor films comprises a current injection region;
~~wherein~~ a current non-injection region formed on both sides of said ridge-like strip on an active layer, wherein said current non-injection region comprises a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$, and wherein the component ratio "x" of Al is between 0.3 and 1.0;
~~and~~

a p-side electrode is formed on and in contact with the current non-injection region; and a film located between the active layer and the current non-injection region, comprising a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0.3 \leq x \leq 1.0$).

26. (Currently Amended) A semiconductor laser light emitting device comprising:
a stack of group III nitride semiconductor films each comprising at least one element selected from the group of aluminum, gallium, indium, and boron;

an upper portion of said stacked film forming a ridge-like stripe for a current injection region;

a current non-injection region formed on both sides of said ridge-like strip, wherein at least part of said current non-injection region is made from a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 1.0$), and wherein the component ratio "x" of Al is between 0.3 and 1.0; and

a contact layer formed on the current injection region, wherein the current non-injection region is formed on both sides of said contact layer; and a film located between the active layer and the current non-injection region, comprising a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0.3 \leq x \leq 1.0$).

27. (Previously Presented) A semiconductor laser light emitting device according to claim 26, wherein the contact layer is formed on the ridge-like stripe.

28. (Previously Presented) A semiconductor laser light emitting device according to claim 27, wherein the contact layer is in contact with the ridge-like stripe.

29. (Previously Presented) A semiconductor laser light emitting device according to claim 26, further comprising a p-side electrode is formed on and in contact with the contact layer.

30. (Currently Amended) A semiconductor laser light emitting device comprising:
a stack of group III nitride semiconductor films;
wherein each group III nitride semiconductor film comprises an element selected from the group consisting of aluminum, gallium, indium, and boron;
wherein, an upper portion of said stack of group III nitride semiconductor films ~~comprises~~ forms a ridge-like stripe for a current injection region;
wherein a current non-injection region formed on both sides of said ridge-like strip current injection region, wherein said current non-injection region comprises a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$; and
~~wherein the group III nitride semiconductor films~~ a film located between ~~an~~ the active layer and the current non-injection region, ~~comprises~~ comprising a material expressed by a chemical formula $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($0.15 \leq x \leq 0.30$), and having ~~have~~ a combined thickness of less than or equal to $0.2 \mu\text{m}$ but greater than zero.